

IN THE CLAIMS:

1. (Currently Amended) A semiconductor device comprising:

    a gate electrode formed over a substrate;

    a gate insulating film formed over the gate electrode;

    a semiconductor film comprising silicon formed over the gate electrode with the gate insulating film interposed there between, said semiconductor film including a channel formation region; and

    source and drain regions comprising silicon formed on said semiconductor film,

    wherein a peak position of a Raman spectrograph of said semiconductor film is shifted to a lower wave number side from 520 cm<sup>-1</sup> lower than 520 cm<sup>-1</sup>.

2. (Original) The semiconductor device according to claim 1 wherein said gate electrode comprises molybdenum.

3. (Original) The semiconductor device according to claim 1 wherein said gate insulating film comprises silicon oxide.

4. (Currently Amended) A semiconductor device comprising:

    a gate electrode formed over a substrate;

    a gate insulating film formed over the gate electrode;

    a semiconductor film comprising silicon formed over the gate electrode with the gate insulating film interposed there between, said semiconductor film including a channel formation region; and

    source and drain regions comprising silicon formed on said semiconductor film,

    wherein a peak position of a Raman spectrograph of said semiconductor film is shifted to a lower wavenumber side from 520 cm<sup>-1</sup> lower than 520 cm<sup>-1</sup> and said semiconductor film has a distortion in the lattice.

5. (Original) The semiconductor device according to claim 4 wherein said gate electrode comprises molybdenum.

6. (Original) The semiconductor device according to claim 4 wherein said gate insulating film comprises silicon oxide.

7. (Currently Amended) A semiconductor device comprising:  
a gate electrode formed over a substrate;  
a gate insulating film formed over the gate electrode;  
a semiconductor film comprising silicon formed over the gate electrode with the gate insulating film interposed therebetween, said semiconductor film including a channel formation region and  
source and drain regions comprising silicon formed on said semiconductor film,

wherein a peak position of a Raman spectrograph of said semiconductor film is shifted to a lower wavenumber side from ~~520 cm<sup>-1</sup>~~ lower than 520 cm<sup>-1</sup> and said semiconductor film has a distortion in the lattice, and the semiconductor film has no barrier against carriers at grain boundaries.

8. (Original) The semiconductor device according to claim 7 wherein said gate electrode comprises molybdenum.

9. (Original) The semiconductor device according to claim 7 wherein said gate insulating film comprises silicon oxide.

10. (Original) The semiconductor device according to claim 1 wherein said gate insulating film comprises silicon oxide containing fluorine.

11. (Original) The semiconductor device according to claim 4 wherein said gate insulating film comprises silicon oxide containing fluorine.

12. (Original) The semiconductor device according to claim 7 wherein said gate insulating film comprises silicon oxide containing fluorine.